

ISC Silicon PNP Power Transistor

2SB871

DESCRIPTION

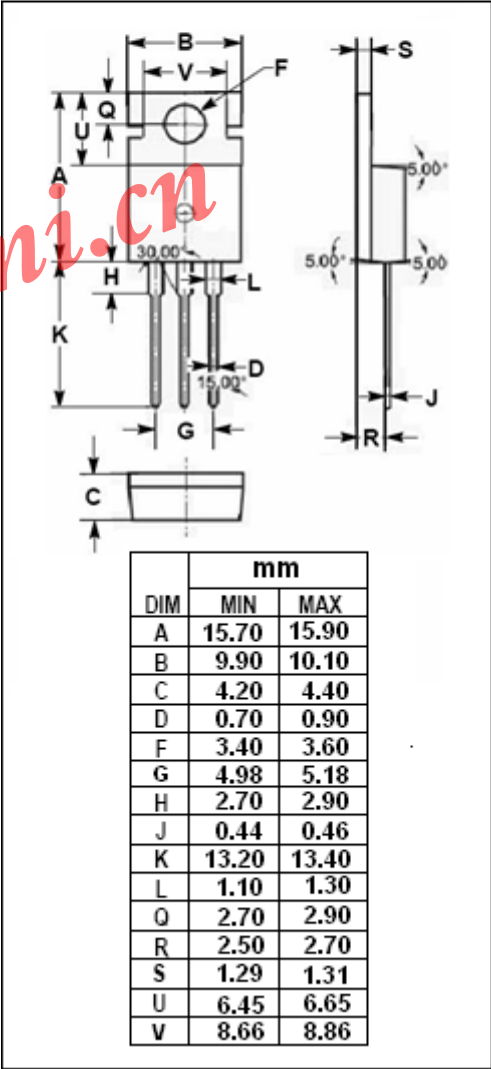
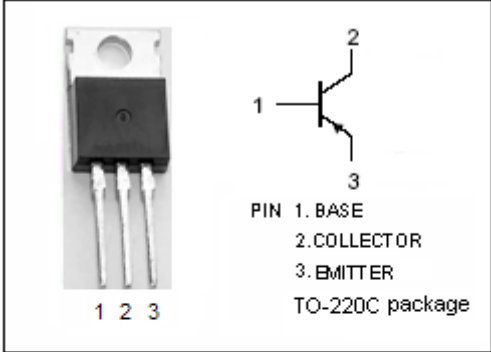
- Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = -20V(\text{Min})$
- High Speed Switching
- Low Collector Saturation Voltage
: $V_{CE(sat)} = -0.6V(\text{Max})@I_C = -10A$

APPLICATIONS

- Designed for low voltage switching applications.

ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-40	V
V_{CEO}	Collector-Emitter Voltage	-20	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-10	A
I_{CM}	Collector Current-Peak	-20	A
P_C	Collector Power Dissipation @ $T_C=25^{\circ}C$	40	W
T_J	Junction Temperature	150	$^{\circ}C$
T_{stg}	Storage Temperature Range	-55~150	$^{\circ}C$



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ELECTRICAL CHARACTERISTICS

 $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C = -10\text{mA}; I_B = 0$	-20			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = -10\text{A}; I_B = -0.33\text{A}$			-0.6	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = -10\text{A}; I_B = -0.33\text{A}$			-1.5	V
I_{CBO}	Collector Cutoff Current	$V_{CB} = -40\text{V}; I_E = 0$			-50	μA
I_{EBO}	Emitter Cutoff Current	$V_{EB} = -5\text{V}; I_C = 0$			-50	μA
h_{FE-1}	DC Current Gain	$I_C = -0.1\text{A}; V_{CE} = -2\text{V}$	45			
h_{FE-2}	DC Current Gain	$I_C = -3\text{A}; V_{CE} = -2\text{V}$	60		260	
C_{OB}	Collector Output Capacitance	$I_E = 0; V_{CB} = -10\text{V}; f = 1\text{MHz}$		400		pF
f_T	Current-Gain Bandwidth Product	$I_C = -0.5\text{A}; V_{CE} = -10\text{V}$		100		MHz

Switching Times

t_{on}	Turn-On Time	$I_C = -3\text{A}; I_{B1} = -I_{B2} = -0.1\text{A}$		0.1		μs
t_s	Storage Time			0.5		μs
t_f	Fall Time			0.1		μs

◆ h_{FE-2} Classifications

R	Q	P
60-120	90-180	130-260